Product data sheet

1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO247 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Values			Unit	
maximum rating						
repetitive peak reverse voltage			6	50		V
average forward current	δ = 0.5; square-wave pulse; T _{mb} ≤ 124 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	16		А		
junction temperature		175		°C		
Parameter	Conditions		Min	Тур	Max	Unit
aracteristics						
forward voltage	I _F = 8 A; T _j = 25 °C; per diode; <u>Fig. 5</u>		-	1.5	1.7	V
	I _F = 8 A; T _j = 150 °C; per diode; <u>Fig. 5</u>		-	1.8	2.2	V
characteristics					,	
recovered charge	$I_F = 8 \text{ A}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $V_R = 400 \text{ V}$; $T_j = 25 \text{ °C}$; per diode; Fig. 7		-	13	-	nC
	repetitive peak reverse voltage average forward current junction temperature Parameter aracteristics forward voltage characteristics	repetitive peak reverse voltage average forward current $\delta = 0.5$; square-wave pulse; $T_{mb} \le 124$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 junction temperature Parameter Conditions aracteristics forward voltage $I_F = 8 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5}$ $I_F = 8 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 5}$ characteristics recovered charge $I_F = 8 \text{ A}; dI_F/dt = 500 \text{ A}/\mu\text{s}; V_R = 400 \text{ V};$	repetitive peak reverse voltage average forward current $\delta = 0.5$; square-wave pulse; $T_{mb} \le 124$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 junction temperature Parameter Conditions aracteristics forward voltage $I_F = 8 \text{ A}$; $T_J = 25$ °C; per diode; Fig. 5 $I_F = 8 \text{ A}$; $T_J = 150$ °C; per diode; Fig. 5 characteristics recovered charge $I_F = 8 \text{ A}$; $I_F = 8 \text$	$\begin{tabular}{ l l l l l l l l l l l l l l l l l l l$	repetitive peak reverse voltage $\delta = 0.5$; square-wave pulse; $T_{mb} \le 124$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 junction temperature $\delta = 0.5$; square-wave pulse; $T_{mb} \le 124$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 $\delta = 0.5$; Fig. 4 $\delta = 0.5$; Fig. 5 $\delta = 0.5$; Fig. 6 $\delta = 0.5$; Fig. 7 $\delta = 0.5$; Fig. 8 $\delta = 0.5$; Fig. 9 $\delta = 0.5$; Fig	repetitive peak reverse voltage $S = 0.5$; square-wave pulse; $S = 124$ °C; both diodes conducting; $S = 124$ °C; $S = 124$ °C; both diodes conducting; $S = 124$ °C; both diodes conducting; $S = 124$ °C;

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		A1
3	A2	anode		K
mb	mb	mounting base; connected to cathode		sym125

6. Ordering information

Table 3. Ordering information

Type number	Package	Orderable part number	Packing	Small packing	Package	Package
	name		method	quantity	version	issue date
WNSC2D16650CW	TO247	WNSC2D16650CWQ	Tube	30	TO247N	20-July-2016

7. Marking

Table 4. Marking codes

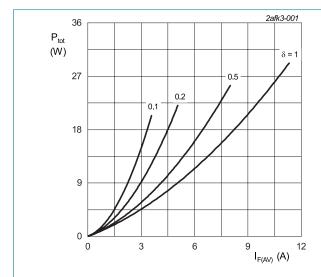
Type number	Marking codes
WNSC2D16650CW	WNSC2D 16650CW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
I _{O(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 124$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	16	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 124 °C; square-wave pulse; per diode	16	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	48	А
		t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode	385	А
l ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$	11.5	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.144 \text{ V; } R_{\text{s}} = 0.1272 \text{ }\Omega \\ \text{Fig. 1.} & \text{Forward power dissipation as a function of average forward current; square waveform; } \\ & \text{maximum values; per diode} \end{split}$$

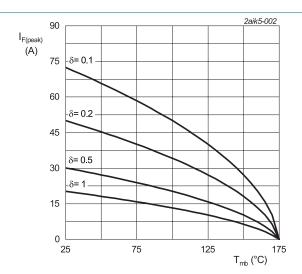


Fig. 2. Current derating as a function of mounting base temperature; per diode

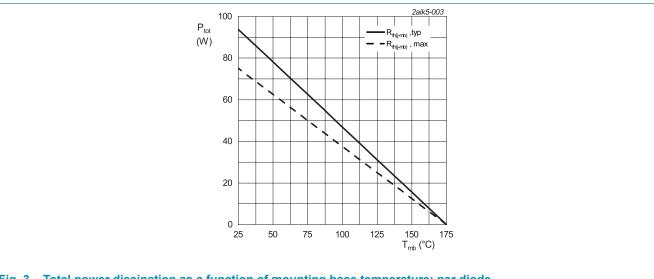
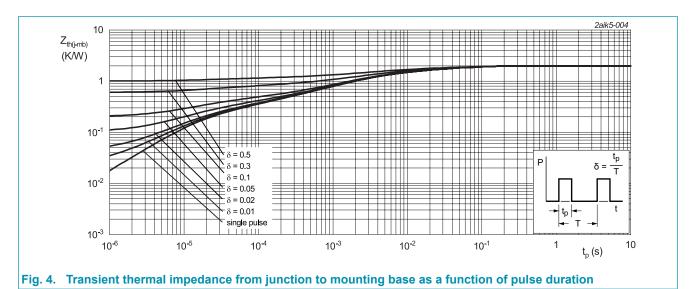


Fig. 3. Total power dissipation as a function of mounting base temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

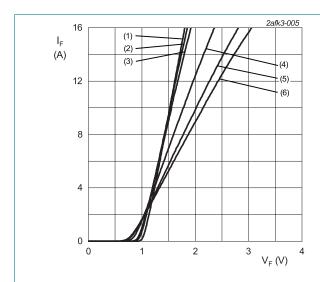
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
uig-iiib)	thermal resistance	per diode; Fig. 4	-	-	2	K/W
	from junction to mounting base	both diodes conducting	-	-	1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	IV	lin T	ур	Max	Unit
Static cha	aracteristics				'		
V_{F}	forward current	I _F = 8 A; T _j = 25 °C; per diode; <u>Fig. 5</u>	-	1	.5	1.7	V
		I _F = 8 A; T _j = 150 °C; per diode; <u>Fig. 5</u>	-	1	.8	2.2	V
		I _F = 8 A; T _j = 175 °C; per diode; <u>Fig. 5</u>	-	2		2.3	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	0	.4	40	μA
		V _R = 650 V; T _j = 175 °C; per diode; <u>Fig. 6</u>	-	2	0	200	μA
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/µs};$ $T_j = 25 \text{ °C}; \text{ per diode}; \frac{\text{Fig. 7}}{\text{C}}$	-	1	3	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	2	60	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	3	1	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	2	7	-	pF
E _{as}	non-repetitive avalanche energy	I_R = 4.9 A; L = 5 mH; $T_{J(init)}$ = 25 °C; per diode	6	0 -		-	mJ



 V_o = 1.144 V; R_s = 0.1272 Ω (1) T_j = -55 °C; typical values

(2) $T_j = 0$ °C; typical values (3) $T_j = 25$ °C; typical values

(4) $T_i = 100 \,^{\circ}\text{C}$; typical values

(5) $T_j = 150$ °C; typical values (6) $T_j = 175$ °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

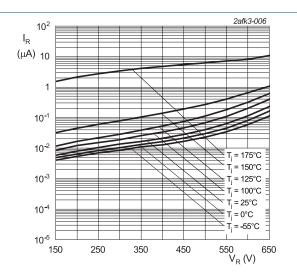


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

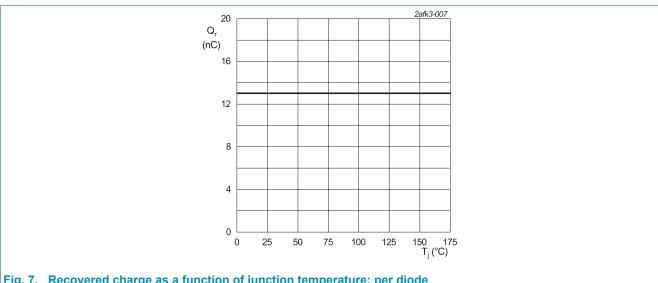
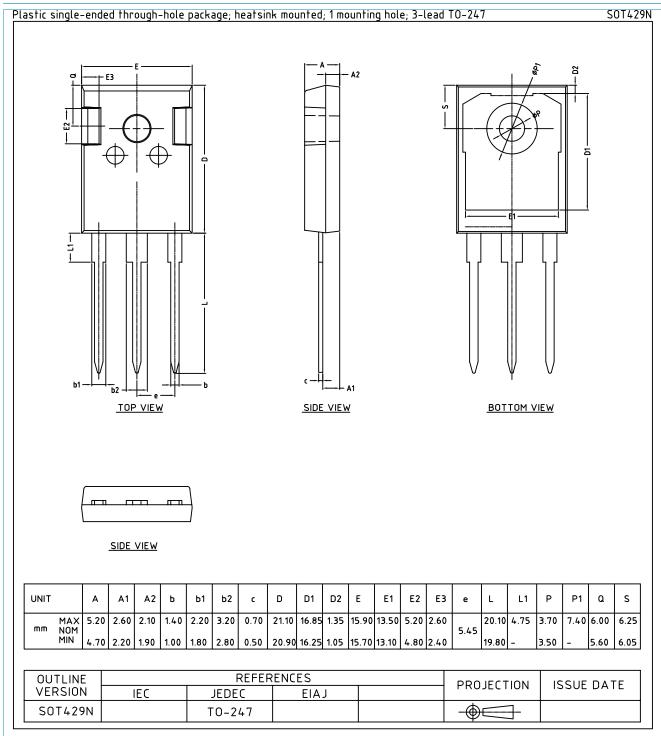


Fig. 7. Recovered charge as a function of junction temperature; per diode

11. Package outline



12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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